

## **BUL89**

# HIGH VOLTAGE FAST-SWITCHING NPN POWER TRANSISTOR

- HIGH VOLTAGE CAPABILITY
- MINIMUM LOT-TO-LOT SPREAD FOR RELIABLE OPERATION
- LOW BASE-DRIVE REQUIREMENTS
- VERY HIGH SWITCHING SPEED
- FULLY CHARACTERIZED AT 125°C

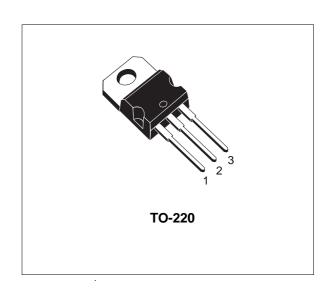
#### **APPLICATIONS**

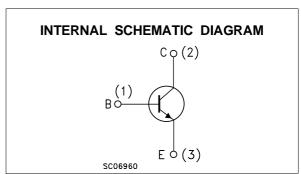
- ELECTRONIC TRANSFORMER FOR HALOGEN LAMPS
- SWITCH MODE POWER SUPPLIES

#### **DESCRIPTION**

The BUL89 is manufactured using high voltage Multiepitaxial Mesa technology for cost-effective high performance. It uses a Hollow Emitter structure to enhance switching speeds.

The BUL series is designed for use in lighting applications and low cost switch-mode power supplies.





#### **ABSOLUTE MAXIMUM RATINGS**

Symbol	Parameter	Value	Unit
$V_{CES}$	Collector-Emitter Voltage (V <sub>BE</sub> = 0)	850	V
$V_{CEO}$	Collector-Emitter Voltage (I <sub>B</sub> = 0)	400	V
V <sub>ЕВО</sub>	Emitter-Base Voltage (Ic = 0)	9	V
Ic	Collector Current	12	А
I <sub>CM</sub>	Collector Peak Current (t <sub>p</sub> < 5 ms)	25	Α
$I_B$	Base Current	6	Α
I <sub>BM</sub>	Base Peak Current (t <sub>p</sub> < 5 ms)	12	Α
P <sub>tot</sub>	Total Dissipation at T <sub>c</sub> = 25 °C	110	W
$T_{stg}$	Storage Temperature	-65 to 150	°C
$T_j$	Max. Operating Junction Temperature	150	°C

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#### THERMAL DATA

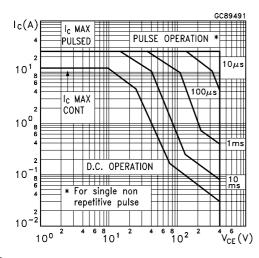
R <sub>thj-case</sub> Thermal Resistance Junction-Case	Max	1.14	°C/W
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## **ELECTRICAL CHARACTERISTICS** (T<sub>case</sub> = 25 °C unless otherwise specified)

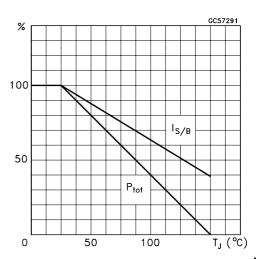
Symbol	Parameter	Test	Conditions	Min.	Тур.	Max.	Unit
I <sub>CES</sub>	Collector Cut-off Current (V <sub>BE</sub> = 0)	V <sub>CE</sub> = 850 V V <sub>CE</sub> = 850 V	T <sub>j</sub> = 125 °C			100 500	μA μA
I <sub>CEO</sub>	Collector Cut-off Current (I <sub>B</sub> = 0)	V <sub>CE</sub> = 400 V				100	μΑ
V <sub>CEO(sus)*</sub>	Collector-Emitter Sustaining Voltage (I <sub>B</sub> = 0)	I <sub>C</sub> = 10 mA	L = 25 mH	400			V
V <sub>EBO</sub>	Emitter-Base Voltage (I <sub>C</sub> = 0)	I <sub>E</sub> = 10 mA		9			V
V <sub>CE(sat)</sub> *	Collector-Emitter Saturation Voltage	I <sub>C</sub> = 5 A I <sub>C</sub> = 8 A I <sub>C</sub> = 12 A	I <sub>B</sub> = 1 A I <sub>B</sub> = 1.6 A I <sub>B</sub> = 2.4 A			1 1.5 5	V V V
V <sub>BE(sat)</sub> *	Base-Emitter Saturation Voltage	I <sub>C</sub> = 5 A I <sub>C</sub> = 8 A	I <sub>B</sub> = 1 A I <sub>B</sub> = 1.6 A			1.3 1.6	V V
h <sub>FE</sub> *	DC Current Gain	I <sub>C</sub> = 5 A I <sub>C</sub> = 10 mA	V <sub>CE</sub> = 5 V V <sub>CE</sub> = 5 V	10 10		40	
t <sub>s</sub> t <sub>f</sub>	INDUCTIVE LOAD Storage Time Fall Time	$I_C = 8 \text{ A}$ $V_{BE(off)} = -5 \text{ V}$ $V_{CL} = 350 \text{ V}$ (see figure 1)	$I_{B1}$ = 1.6 A $R_{BB}$ = 0 $\Omega$ L = 200 $\mu$ H		1.5 55	2.3 110	μs ns
t <sub>s</sub> t <sub>f</sub>	INDUCTIVE LOAD Storage Time Fall Time	$I_{C} = 8 \text{ A}$ $V_{BE(off)} = -5 \text{ V}$ $V_{CL} = 350 \text{ V}$ $T_{j} = 100 \text{ °C}$	$I_{B1} = 1.6 \text{ A}$ $R_{BB} = 0 \Omega$ $L = 200 \mu\text{H}$ (see figure 1)		1.9 80		μs ns

<sup>\*</sup> Pulsed: Pulse duration = 300 μs, duty cycle 1.5 %

## Safe Operating Area

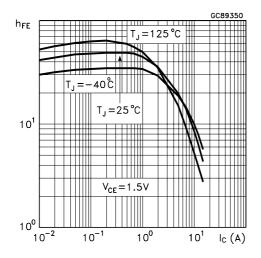


### **Derating Curve**

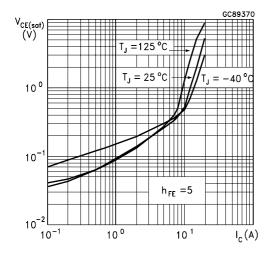


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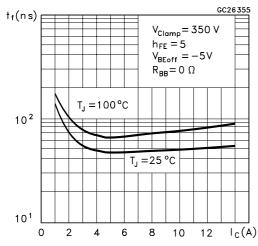
#### DC Current Gain



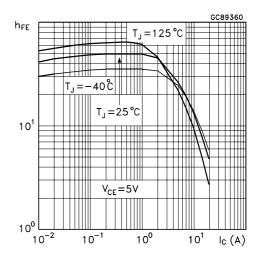
#### Collector Emitter Saturation Voltage



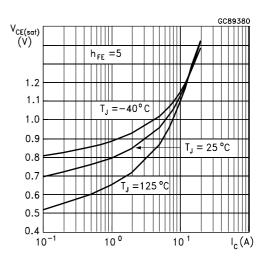
#### Inductive Load Fall Time



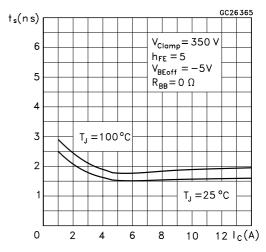
#### DC Current Gain



#### Base Emitter Saturation Voltage



#### Inductive Load Storage Time



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#### Reverse Biased SOA

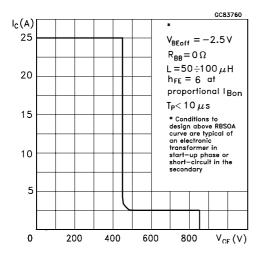
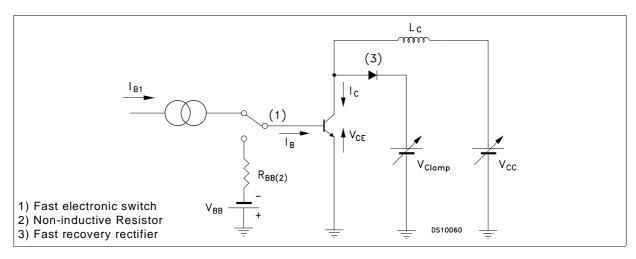


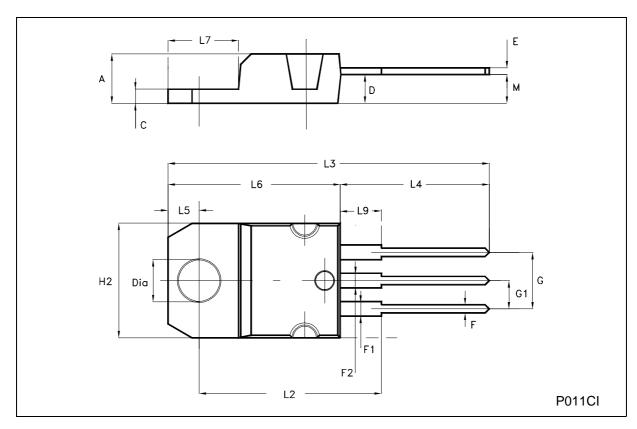
Figure 1: Inductive Load Switching Test Circuit



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## **TO-220 MECHANICAL DATA**

DIM.		mm			inch	
DIWI.	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
Α	4.40		4.60	0.173		0.181
С	1.23		1.32	0.048		0.052
D	2.40		2.72	0.094		0.107
Е	0.49		0.70	0.019		0.027
F	0.61		0.88	0.024		0.034
F1	1.14		1.70	0.044		0.067
F2	1.14		1.70	0.044		0.067
G	4.95		5.15	0.194		0.202
G1	2.40		2.70	0.094		0.106
H2	10.00		10.40	0.394		0.409
L2		16.40			0.645	
L4	13.00		14.00	0.511		0.551
L5	2.65		2.95	0.104		0.116
L6	15.25		15.75	0.600		0.620
L7	6.20		6.60	0.244		0.260
L9	3.50		3.93	0.137		0.154
М		2.60			0.102	
DIA.	3.75		3.85	0.147		0.151



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